

S/N 09/135,413

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Serial No.: 09/135,413

Filed: August 14, 1998

Title: METHOD FOR OPERATING A DEAPROM HAVING AN AMORPHOUS SILICON CARBIDE GATE INSULATOR

Examiner: Viet Q. Nguyen

Group Art Unit: 2818

Docket: 303.354US2

PATENT

AMENDMENT AND RESPONSE

Assistant Commissioner for Patents
Washington, D.C. 20231

In response to the Office Action mailed July 9, 1999, please amend the above identified patent application as follows:

IN THE CLAIMS

Please amend the claims as follows:

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15 43. (Amended) A method for operating a floating gate transistor comprising:
programming the floating gate transistor by inducing charge to migrate from a channel in a substrate through [a] an amorphous silicon carbide (a-SiC) gate insulator to a floating gate electrode in the floating gate transistor; and

erasing the floating gate transistor by inducing charge to migrate from the floating gate electrode through the amorphous silicon carbide (a-SiC) gate insulator to the channel.

16 44. (Amended) The method of claim 43 wherein:

programming comprises programming the floating gate transistor by inducing hot electron injection from a channel in a substrate through [an] the amorphous silicon carbide (a-SiC) gate insulator to a polysilicon floating gate electrode in the floating gate transistor; and

erasing comprises erasing the floating gate transistor by inducing charge to migrate from the polysilicon floating gate electrode through the amorphous silicon carbide (a-SiC) gate insulator to the channel through Fowler-Nordheim tunneling.

19 47. (Amended) A method for operating a floating gate transistor connected to a control line and a data line, the method comprising:

programming the floating gate transistor by providing a control voltage on the control